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STD16N65M2

N-channel 650 V, 0.32 Ω typ., 11 A MDmesh M2 Power MOSFET in a DPAK package

Datasheet – production data

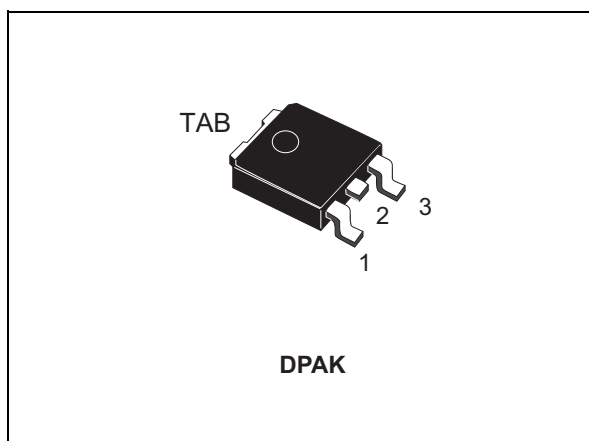
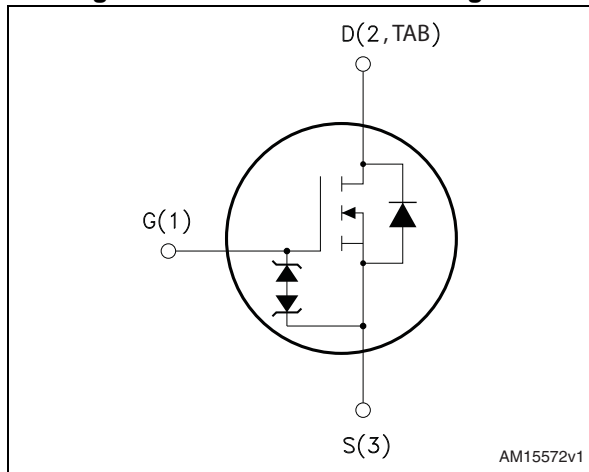


Figure 1. Internal schematic diagram



Features

Order code	$V_{DS} @ T_{Jmax}$	$R_{DS(on) max}$	I_D
STD16N65M2	710 V	0.36 Ω	11 A

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1. Device summary

Order codes	Marking	Package	Packaging
STD16N65M2	16N65M2	DPAK	Tape and reel

Contents

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Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	11	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	6.9	A
$I_{DM}^{(1)}$	Drain current (pulsed)	44	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	110	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature		

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 11\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD}=400\text{ V}$.
3. $V_{DS} \leq 520\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.14	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}$	Thermal resistance junction-pcb max ⁽¹⁾	50	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch² FR-4, 2 Oz copper board

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	1.9	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25\text{ }^\circ\text{C}$, $I_D=I_{AR}$; $V_{DD}=50$)	360	mJ

Electrical characteristics

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2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 650\text{ V}$			1	μA
		$V_{GS} = 0, V_{DS} = 650\text{ V}, T_C = 125\text{ °C}$			100	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 25\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}$		0.32	0.36	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{GS} = 0, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	718	-	pF
C_{oss}	Output capacitance		-	32	-	pF
C_{rss}	Reverse transfer capacitance		-	1.1	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$	-	189	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	5.2	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 11\text{ A}, V_{GS} = 10\text{ V}$ (see Figure 15)	-	19.5	-	nC
Q_{gs}	Gate-source charge		-	4	-	nC
Q_{gd}	Gate-drain charge		-	8.3	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

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Electrical characteristics
Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 5.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14 and 19)	-	11.3	-	ns
t_r	Rise time		-	8.2	-	ns
$t_{d(off)}$	Turn-off delay time		-	36	-	ns
t_f	Fall time		-	11.3	-	ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		11	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		44	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0$, $I_{SD} = 11\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 11\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 16)	-	342		ns
Q_{rr}	Reverse recovery charge		-	3.5		μC
I_{RRM}	Reverse recovery current		-	20.4		A
t_{rr}	Reverse recovery time	$I_{SD} = 11\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16)	-	458		ns
Q_{rr}	Reverse recovery charge		-	4.6		μC
I_{RRM}	Reverse recovery current		-	20.5		A

1. Pulse width limited by safe operating area

 2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Electrical characteristics

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2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

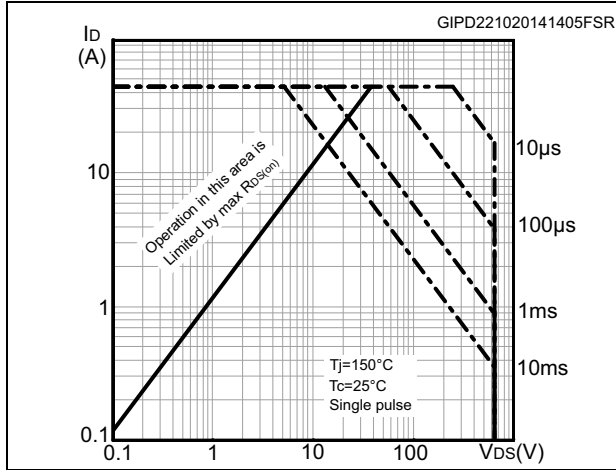


Figure 3. Thermal impedance

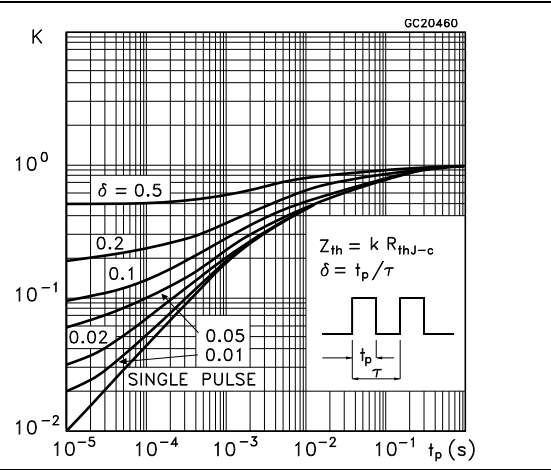


Figure 4. Output characteristics

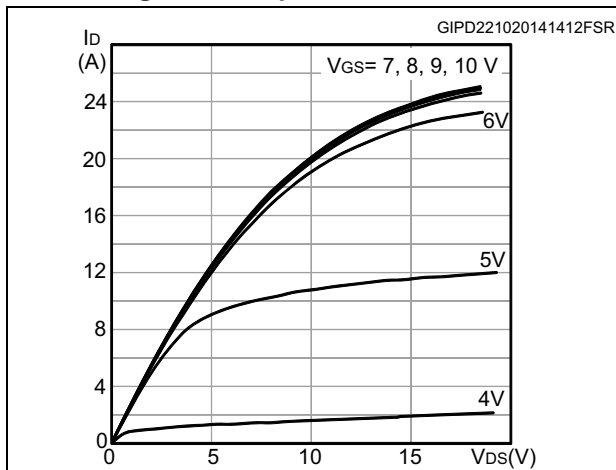


Figure 5. Transfer characteristics

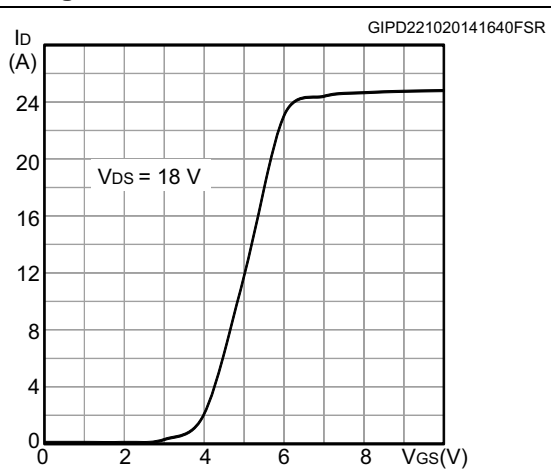


Figure 6. Normalized gate threshold voltage vs. temperature

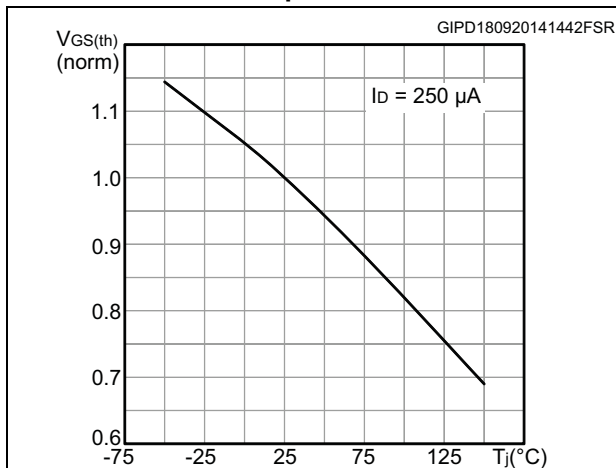
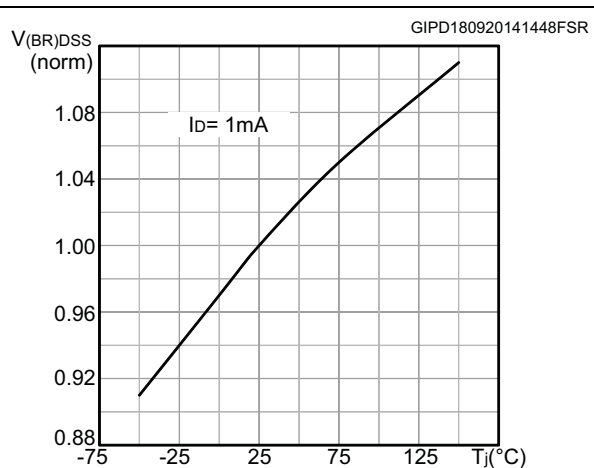


Figure 7. Normalized $V_{(BR)DSS}$ vs. temperature



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Electrical characteristics

Figure 8. Static drain-source on-resistance

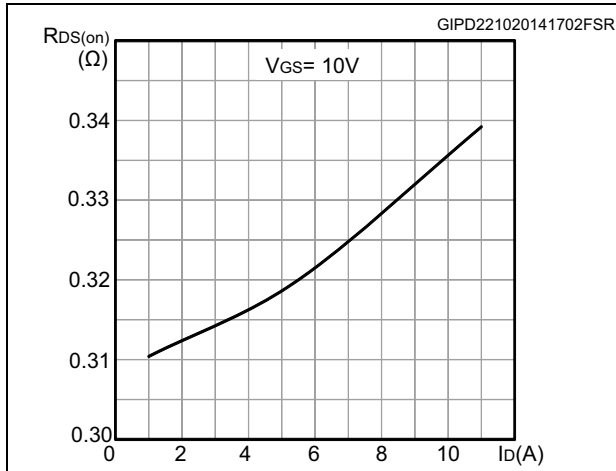


Figure 9. Normalized on-resistance vs. temperature

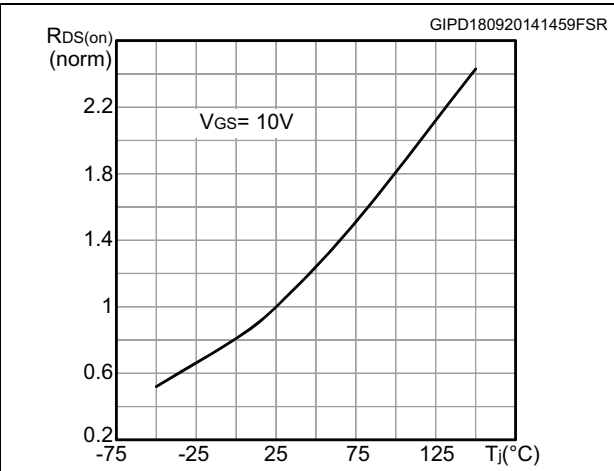


Figure 10. Gate charge vs. gate-source voltage

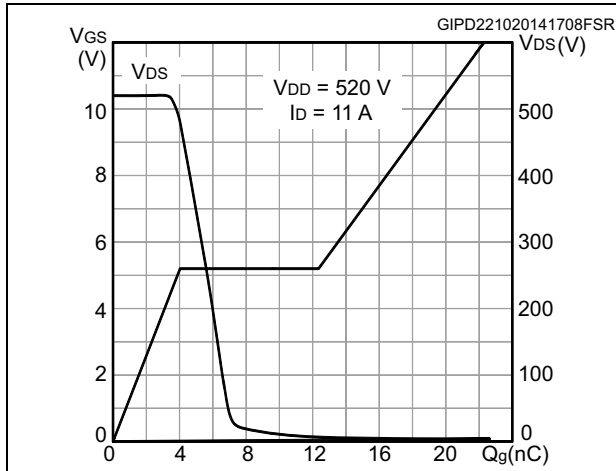


Figure 11. Capacitance variations

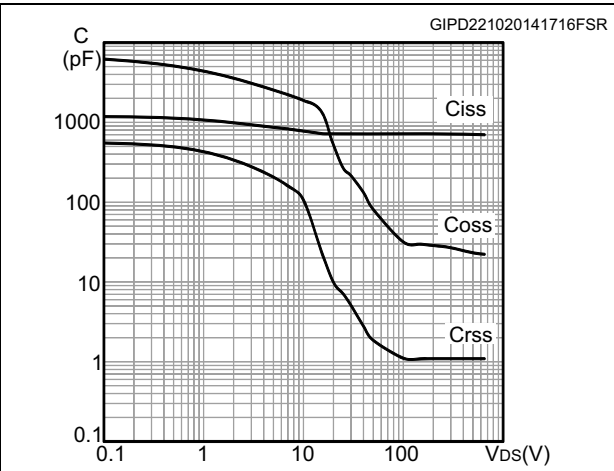


Figure 12. Output capacitance stored energy

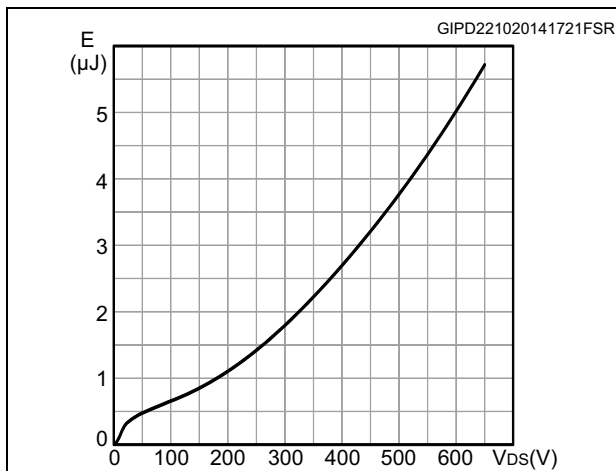
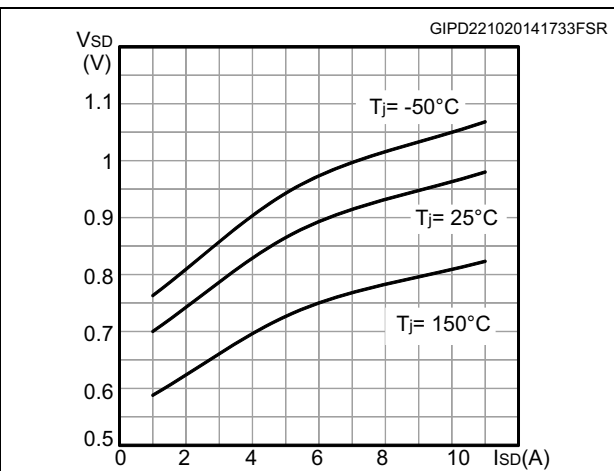


Figure 13. Source-drain diode forward characteristics



3 Test circuits

Figure 14. Switching times test circuit for resistive load

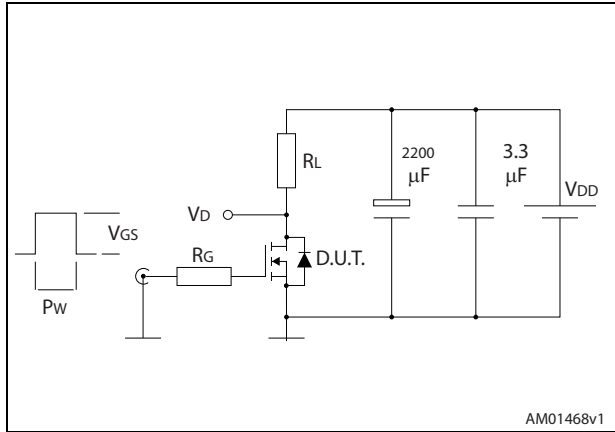


Figure 15. Gate charge test circuit

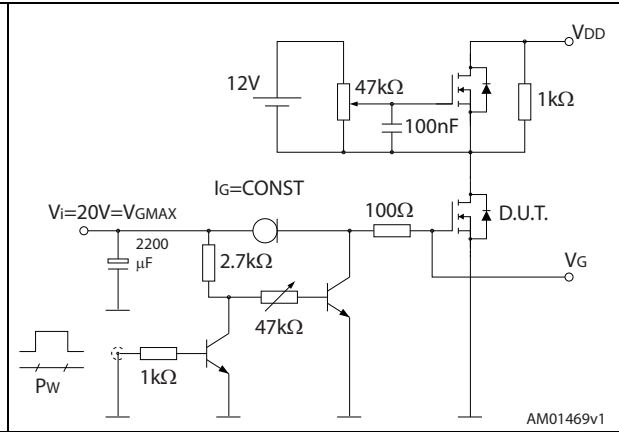


Figure 16. Test circuit for inductive load switching and diode recovery times

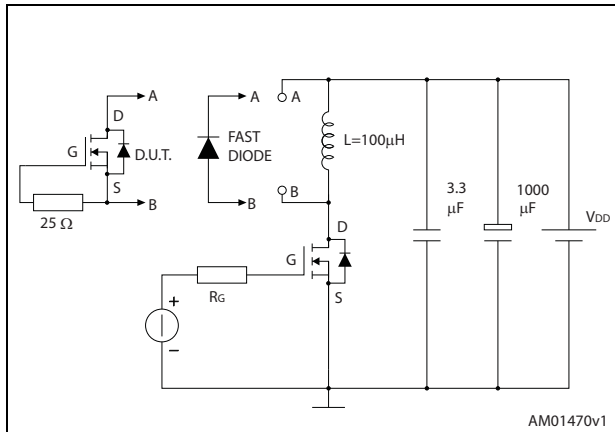


Figure 17. Unclamped inductive load test circuit

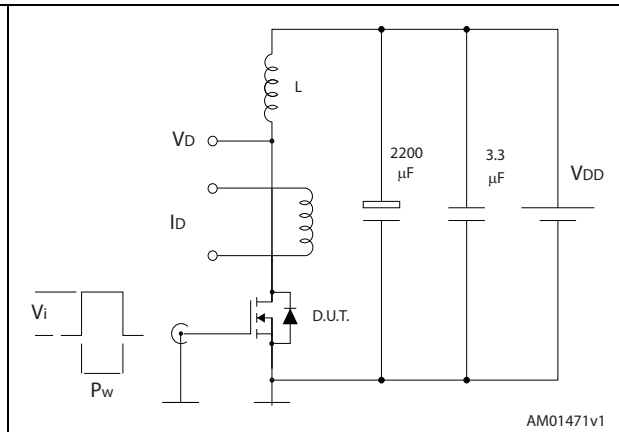


Figure 18. Unclamped inductive waveform

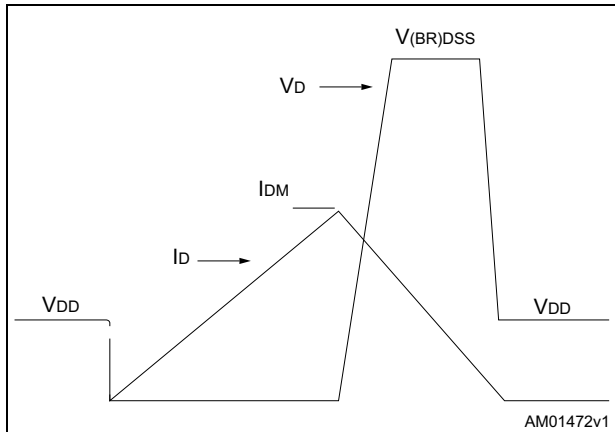
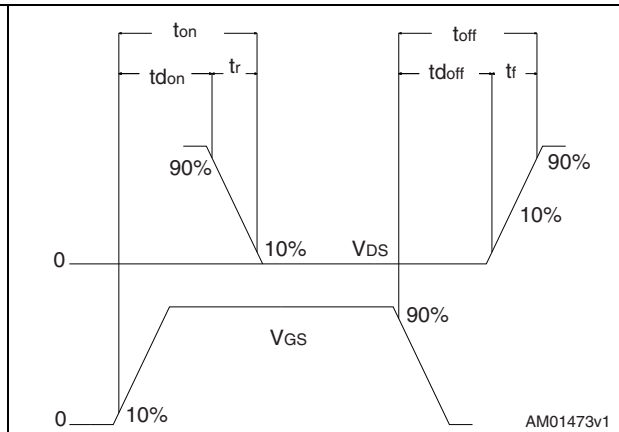


Figure 19. Switching time waveform



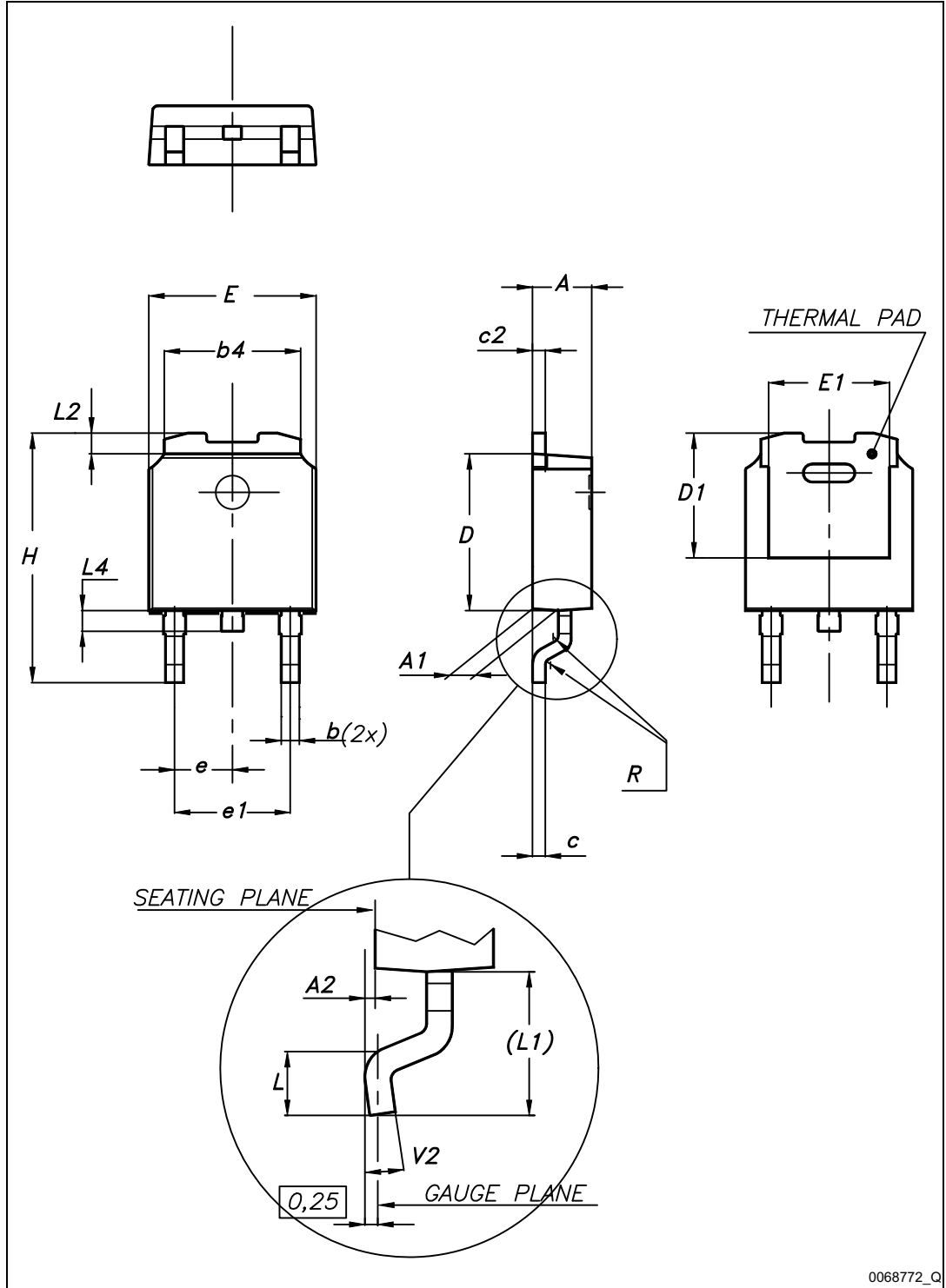
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Package mechanical data

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Figure 20. DPAK (TO-252) type A drawing



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Package mechanical data

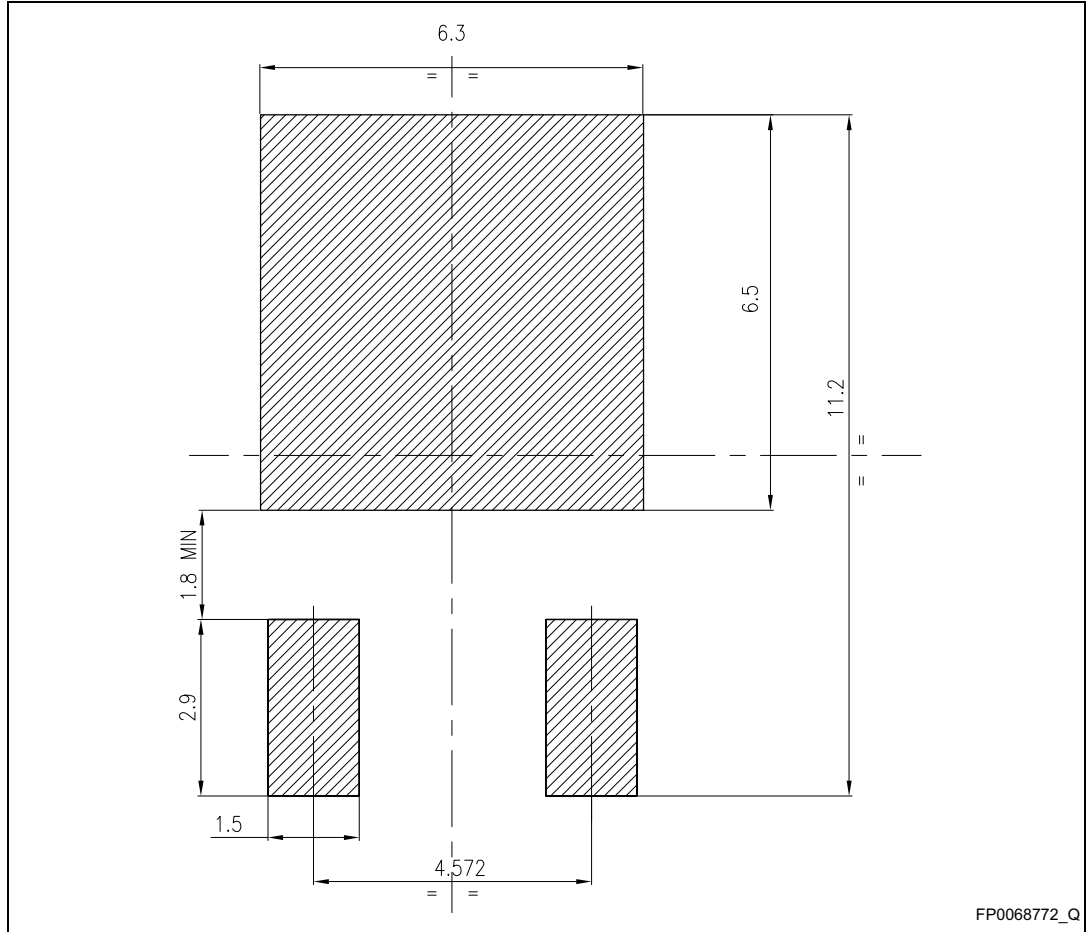
Table 9. DPAK (TO-252) type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1.00		1.50
L1		2.80	
L2		0.80	
L4	0.60		1.00
R		0.20	
V2	0°		8°

Package mechanical data

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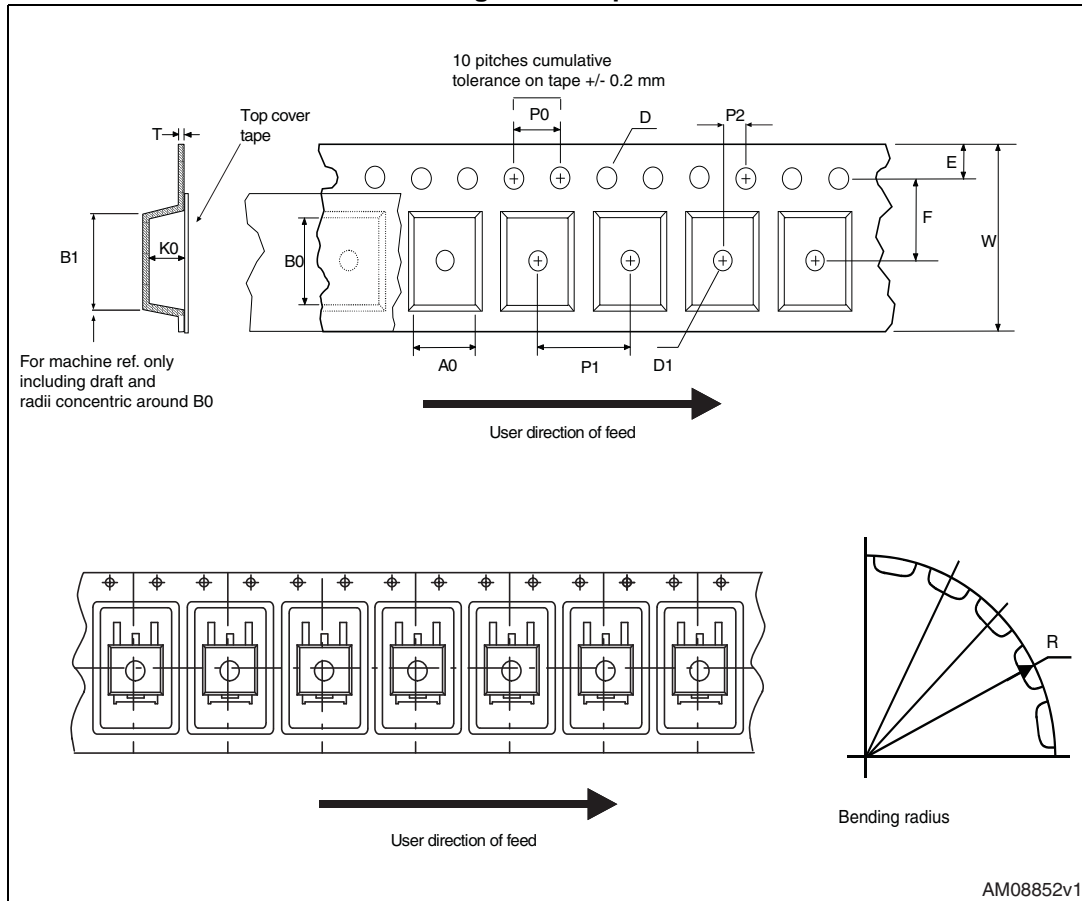
Figure 21. DPAK (TO-252) footprint (a)



a. All dimensions are in millimeters

5 Packaging mechanical data

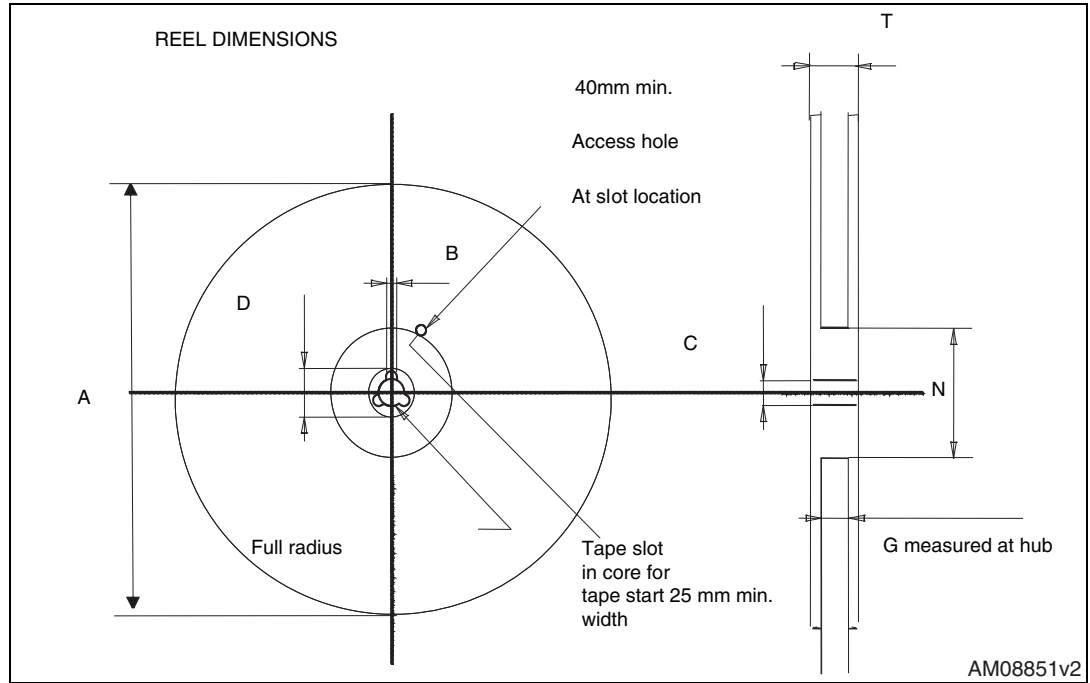
Figure 22. Tape



Packaging mechanical data

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Figure 23. Reel



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Packaging mechanical data

Table 10. DPAK (TO-252) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	6.8	7	A		330
B0	10.4	10.6	B	1.5	
B1		12.1	C	12.8	13.2
D	1.5	1.6	D	20.2	
D1	1.5		G	16.4	18.4
E	1.65	1.85	N	50	
F	7.4	7.6	T		22.4
K0	2.55	2.75			
P0	3.9	4.1	Base qty.		2500
P1	7.9	8.1	Bulk qty.		2500
P2	1.9	2.1			
R	40				
T	0.25	0.35			
W	15.7	16.3			

6 Revision history

Table 11. Document revision history

Date	Revision	Changes
24-Oct-2014	1	First release.

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